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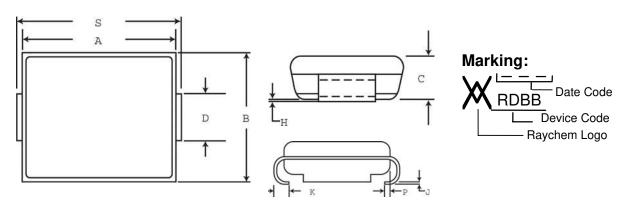
SiBar™ Thyristor Surge Protectors

PRODUCT: TVB200SA

DOCUMENT: SCD 24304 PCN: 732781 REV LETTER: E REV DATE: AUGUST 24, 2004 PAGE NO.: 1 OF 2

Specification Status: RELEASED

PHYSICAL DESCRIPTION



1

	Α		E	3	C	;	D	**	F	1	,	J	ł	(
	MIN	MAX												
mm:	4.06	4.57	3.30	3.81	1.90	2.41	1.96	2.11	0.051	0.152	0.15	0.30	0.76	1.27
in*:	(0.160)	(0.180)	(0.130)	(0.150)	(0.075)	(0.095)	(0.077)	(0.083)	(0.002)	(0.006)	(0.006)	(0.012)	(0.030)	(0.050)

	Р	S				
	REF	MIN	MAX			
mm:	0.51	5.21	5.59			
in*:	(0.020)	(0.205)	(0.220)			

(0.020) | (0.205) | (0.220) *Rounded off approximation

** D DIMENSION SHALL BE MEASURED WITHIN DIMENSION P

Other Physical Characteristics

SMB (Surface Mount, JEDEC DO-214AA Package)
Tin / lead finish
Epoxy, meets UL94 V-0 requirements
per MIL-STD-750, Method 2026
per MIL-STD-750, Method 2031
per MIL-STD-750, Method 1022
per MIL-STD-750, Method 2016
per MIL-STD-750, Method 2056

Tape and Reel packaging per EIA 481-1

Agency Recognition:	UL
Precedence:	This specification takes precedence over documents referenced herein.
CAUTION:	Operation beyond the rated voltage or current may result in rupture, electrical arcing or flame.

Materials Information ELV Compliant

Directive 2000/53/EC Compliant

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DEVICE RATINGS @ 25º C (Both Polarities)

	Parameter	Symbol	Value	Units
Repetitive off-State Vo	ltage, Maximum at ID = 5 μA	VDM	200	V
Non-Repetitive Peak	Telcordia GR-1089 CORE 10x1000 μs	IPP ₁	50	A
Impulse Current	TIA-968 lightning Type A Metallic 10/560 µs	IPP ₂	70	А
Double exponential	TIA-968 lightning Type A Longit. 10/160 µs	IPP ₃	100	A
Waveform	Telcordia GR-1089 Intrabuilding 2/10 µs	IPP ₄	150	A
(Notes 1 and 2)	IEC61000-4-5 (Voc 1.2/50us) 8/20 µs	IPP ₅	150	A
	ITU-T K.20/K.21 (Voc 10/700us) 5/310 µs	IPP ₆	90	A
	TIA-968 lightning Type B (Voc 9/720us) 5/320 µs	IPP ₇	90	A
Critical Rate of Rise of				
Powered Pulse Amplifie	di/dt	500	A/µs	
Maximum 2x10 usec w	aveform, Voc=750V, Isc=150A peak	di/dt	110	A/us

DEVICE THERMAL RATINGS

Storage Temperature Range	TSTG	-55 to 150	⁰C
Operating Temperature Range	TA	-40 to 125	°C
Blocking or conducting state			
Overload Junction Temperature	TJ	+150	°C
Maximum; Conducting state only			
Maximum Lead Temperature for Soldering Purpose; for 10 seconds	TL	+260	°C

ELECTRICAL CHARACTERISTICS Both polarities (TJ @ 25°C unless otherwise noted)

Characteristics	-	Symbol	Min	Тур	Max	Units
Breakover Voltage (dv/dt = $0.4kV/\mu$ sec, I _{SC} =900mA, V _{DC} = 500V (bot	(+25ºC) h polarities))	VBO		260	320	V
Breakover Voltage Temperature Coefficient		dVBO/dTJ		0.1		%/ºC
Off-State Current	(VD1=50V)	ID1			2.0	μA
	(VD2=VDM)	ID2			5.0	μA
On-State Voltage	(IT=1A)	VT			4.0	V
$(PW \le 300 \ \mu sec, Duty Cycle \le 2\% \ (Note 2))$						
Breakover Current		IBO			800	mA
Holding Current (Note 2)		IH	150			mA
Peak Onstage Surge Current (Measured @ 60Hz, 1 cycle, 600V)	ITSM	22			A	
Critical Rate of Rise of Off-State Voltage (Linear waveform, $V_D = 0.8 \text{ X}$ Rated V_{BO} , $T_J = +25^{\circ}$	dv/dt	2000			V/µs	
Capacitance (f=1.0 Mhz, 50V _{DC}	bias, 1 Vrms)	C1		18		pF
(f=1.0 Mhz, 2V _{DC}	bias, 1 Vrms)	C2		35		pF

Note 1. Allow cooling before test second polarity

Note 2. Measured under pulse conditions to reduce heating

VOLTAGE-CURRENT CHARACTERISTIC

